



TO-92L Plastic-Encapsulate Transistors

2SC2236 TRANSISTOR (NPN)

FEATURE

Complementary to 2SA966 and 3 Watts output Applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

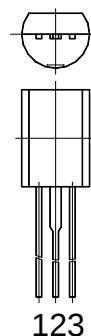
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

TO-92L

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=1\text{mA}$, $I_E=0$	30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=10\text{mA}$, $I_B=0$	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=1\text{mA}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}$, $I_C=500\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5\text{A}$, $I_B=0.03\text{A}$			2	V
Base-emitter voltage	V_{BE}	$I_C=500\text{mA}$, $V_{CE}=2\text{V}$			1	V
Transition frequency	f_T	$V_{CE}=2\text{V}$, $I_C=500\text{mA}$		120		MHz
Collector output Capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

Typical Characteristics

2SC2236

